

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVU005** is a Common Emitter Device Designed for High Linearity Class A Television Band IV and V Transmitters.

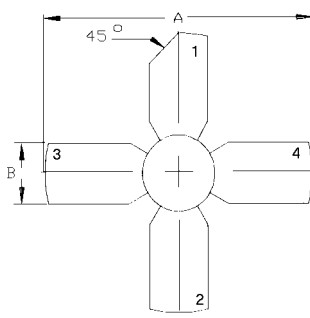
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

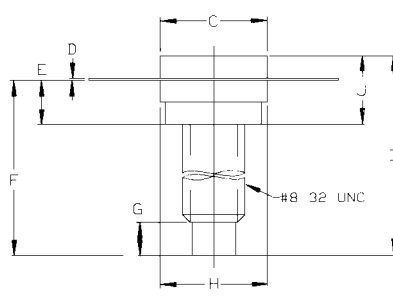
MAXIMUM RATINGS

I_C	500 mA
V_{CB}	45 V
P_{DISS}	8.0 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	22.0 °C/W

PACKAGE STYLE .280 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.055/26.80
B	.220/5.59	.230/5.84
C	.270/6.86	.285/7.24
D	.003/0.08	.007/0.18
E	.117/2.97	.137/3.48
F	.5/2/14.53	
G	.130/3.30	
H	.275/6.99	.285/7.24
I	6.40/16.26	
J	.175/4.45	.21/75.51



1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 20 mA	24			V
BV_{CBO}	I _C = 1.0 mA	45			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		120	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz		5.0		pF
P_G IMD₃	V _{CE} = 20 V I _C = 220 mA Pref = 0.5 W VISION CARRIER = -8.0 dB f = 860 MHz SOUND CARRIER = -7.0 dB CHROMA = -16 dB	10	11	-58	dB